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# Overview of Surface Measurements: What Do Surface Studies Tell Us about Q-Slope ?

High gradient Q-slope vs baking influence

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# Preamble

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- In the following **TB** stand for "textbook", namely:
  - Oxides & oxide films, J. Diggle, Editor. 1973, 2<sup>nd</sup> Ed 1981, New York. 5 volumes = « the Bible »
  - Encyclopedia of Electrochemistry of the Elements, A.J. Bard, Editor. 1974, M. Dekker: New York
  - University Lectures : solid state physics, metallurgy, band structure, electrochemistry...
- A tribute to J. Halbritter, but....

Source	J. Halbritter [1]	More recent [ <i>Antoine, Ma, Kowalski...</i> ]
Nb RRR	90	250-300
Oxide thickness @ eq.	~ 6 nm	< 5nm
Time to reach eq. (H <sub>2</sub> O)	Some mn	4h => 1 week !

**Nb reacts ≠ when purity ↑**

# Usual suspects...

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Surface modification upon baking :

- Modification of adsorbed layers : H<sub>2</sub>O, hydrocarbides,...
- Modification of the oxide layer
- Diffusion of light species (interstitials) : H, C, F... O

Experiments on baked cavities :

- No effect of exposure to air or water (HPR) [[Visentin](#)]
- No difference when baking in air [[Visentin](#)], (known to built up oxide layer [[TB, ...Hellwig](#)], )

**Diffusing species are the most probable suspects**

# Limits of RF measurement

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- RF measurements @ 2K => ~ 50-100 nm,
- RF measurements @ 10K => ~1 $\mu$ m

But

- we are dealing with nm scale modifications !
- => We cannot measure very local modification of SC parameters with cavities.

Susceptibility @  $B > B_{c_2}^{\text{bulk}}$  (=>  $B_{c_2}^{\text{surf}} \equiv B_{c_3}$ ?)

[Steffen, *Casalbuoni*]

- Baking doesn't change bulk properties
- $B_{c_2}^{\text{surf}} > B_{c_2}^{\text{bulk}}$ ; higher for EP than BCP
- Further increased upon baking

# Hydrogen case

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- Hydrogen is  $10^{15}$  times more mobile than O or C [*Alefeld*].
- Hydrogen segregates near the surface [*TB, Antoine,...*]
- Upon baking : will diffuse uniformly inside the material (possibly very few outside with  $\uparrow$  of T)
- Upon cooling, and staying @ RT : will diffuse to the surface and form segregates again, within hours (days ?).

**=> Should rule out hydrogen as a suspect !**

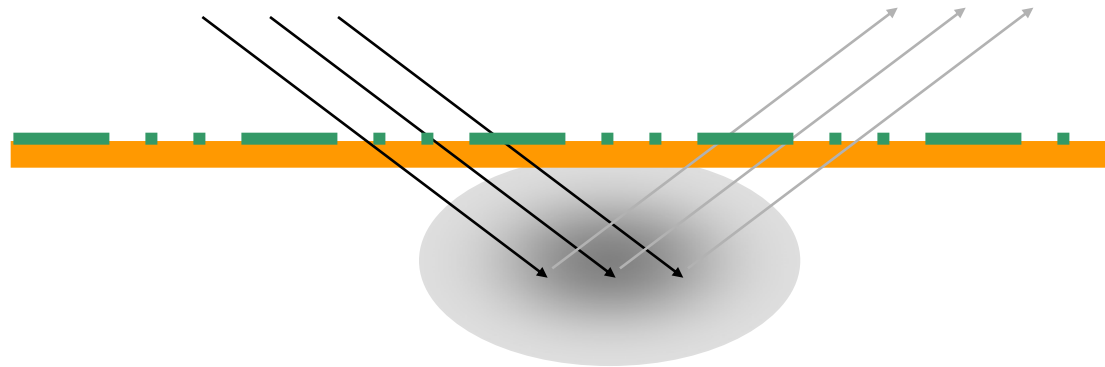
- contradiction with [*Giovati*]?

# What surface technique ?

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Need for sensitivity and depth resolution

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- too superficial => STM, LEED, REED...
  - need to cross  $\sim 5$  nm  $\text{Nb}_2\text{O}_5$ , only indirect info on the SC matrix;
- too “deep” => EDX, electron probe...
  - Explores  $\sim 1$   $\mu\text{m}$  depth
  - Only relative information
- roughness sensitive => X-Rays, reflectometry...
  - Work on monoXstal, special sample prepn

# Profiling techniques

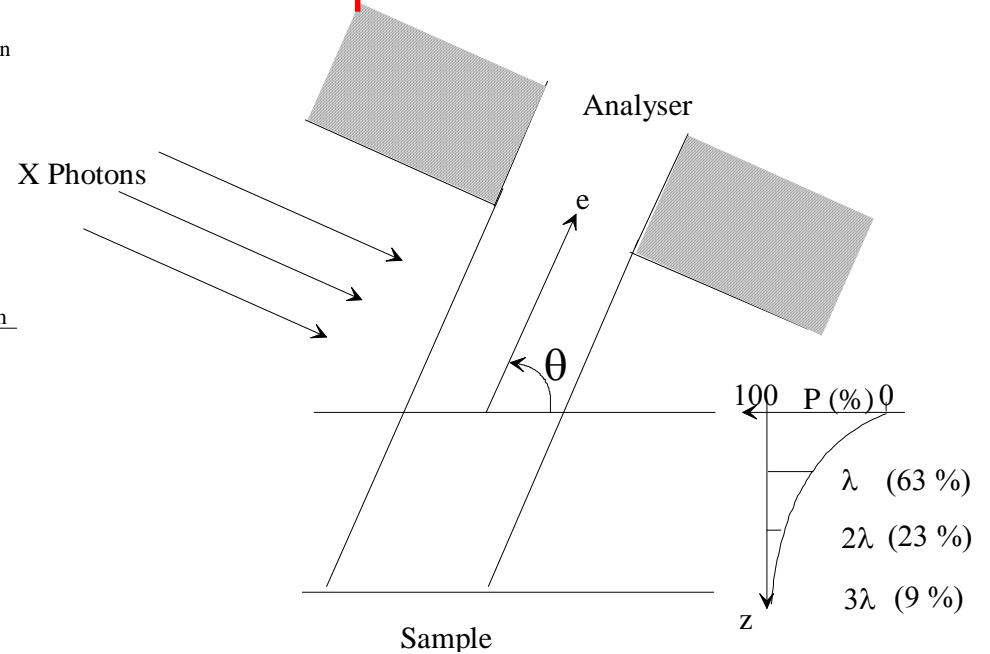
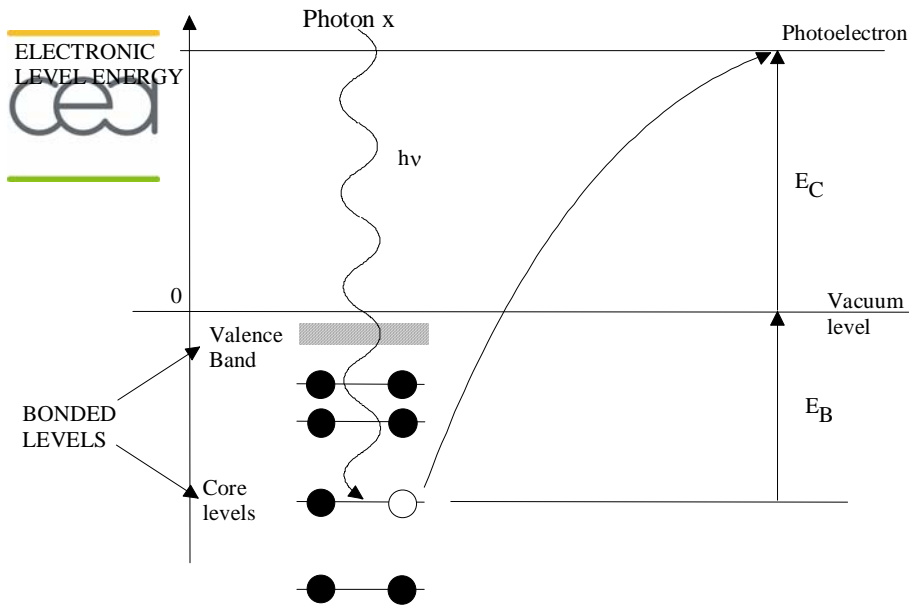
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- Ion sputtering : troubles with preferential O sputtering...
  - Reduces depth sensitivity to  $\sim >10$  nm
  - Only relative information, no way to tell oxide/ $O_i$
- Thus : be careful with profiling (XPS, Auger.... and SIMS in standard conditions)
- Profiling with depth sensitivity :
  - TOF-SIMS (but can't tell oxides /  $O_i$ )
  - Angle-resolved techniques
- Angle resolved photoemission (XPS/ESCA)
  - Chemical sensitivity
  - Profiling
  - But ....

# Photoemission ( $\equiv$ ESCA $\equiv$ XPS) / Auger

A unique way to get info from depth under oxide



$E_B = h\nu - E_C$

$E_B$  (bonding energy) is characteristic from one element ; and is influenced by electronegativity of bonded neighbors  $\Rightarrow$  chemical environment information.

- $\lambda \sim 0.5-2\text{nm}$  (Auger)
  - $\lambda \sim 5\text{nm}$  (XPS)
- But :
- Not very sensitive (0.5 At%)
  - Deconvolution = very « tricky »

For  $[x_i] < 10\%$ ,  $\exists$  deconvolution signal  $\neq$   $\exists$  physical cpd !!!



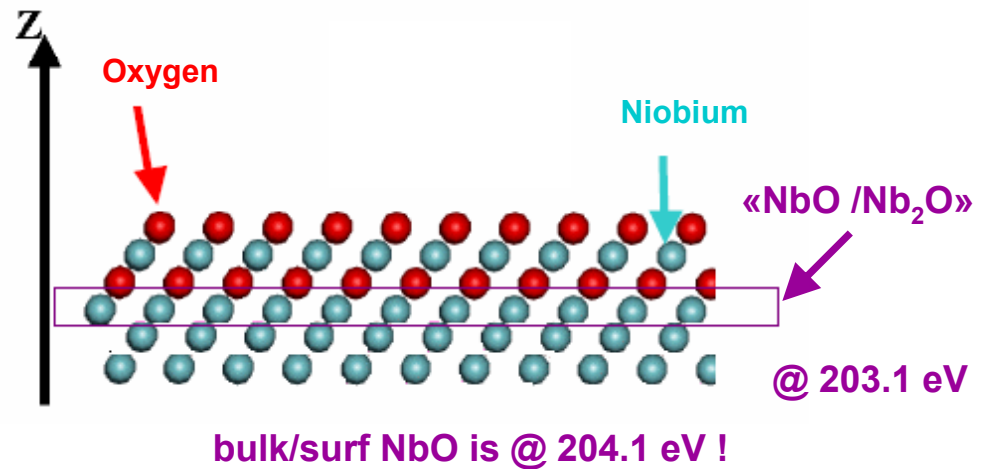
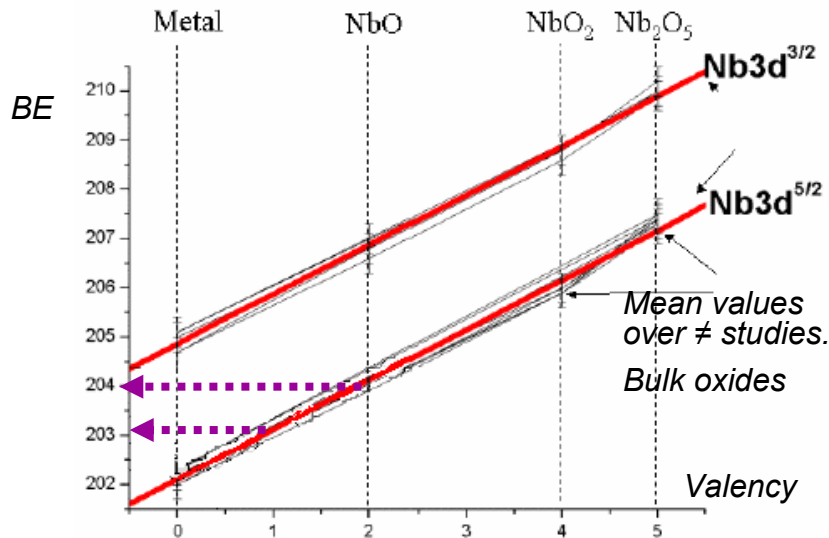
# « Much ado about ~~nothing~~ ... suboxides »

Suboxide (known phases = NbO, NbO<sub>2</sub>) ≠ interstitials oxygens (O<sub>i</sub>)

(standard XPS):



- If observed by profiling (ion sputtering) => you've just created them !
- If observed by deconvolution : be careful !!! if [x] ≤ 10% => not significant with XPS alone !
- Should have precise B. E. (fig 1). Displacements caused by :
  - Interface or mixed state [Arfaoui, Hellwig] (fig 2)
  - Adsorbed species or dangling bond => surface polarization (valid only if thickness << 5 nm) [TB]
  - Interstitial oxygen inside the oxide/metal (seen by RBS [Hellwig], inferred in case of baking)



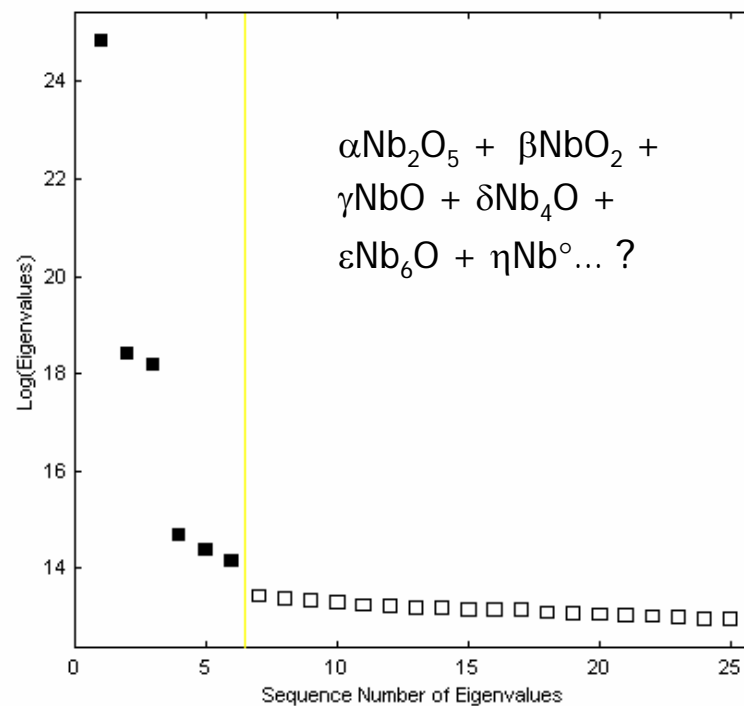
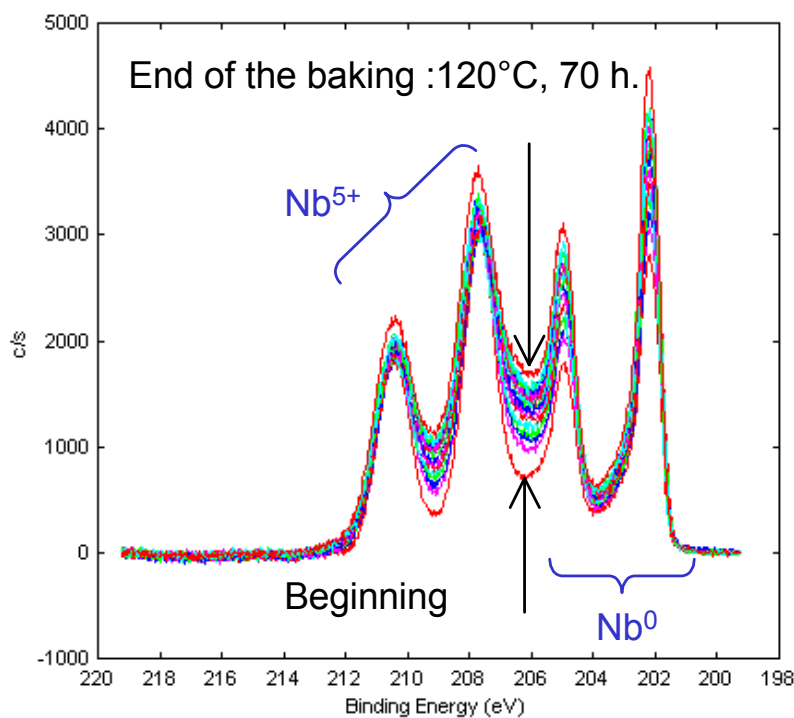
**NbO /Nb<sub>2</sub>O = INTERFACE => ~1-2 monolayer. Not a PHASE !**

# Photoemission : proof of $\exists$ Ox/Suboxides

[Chincarini]



## Principal Components Analysis: ...

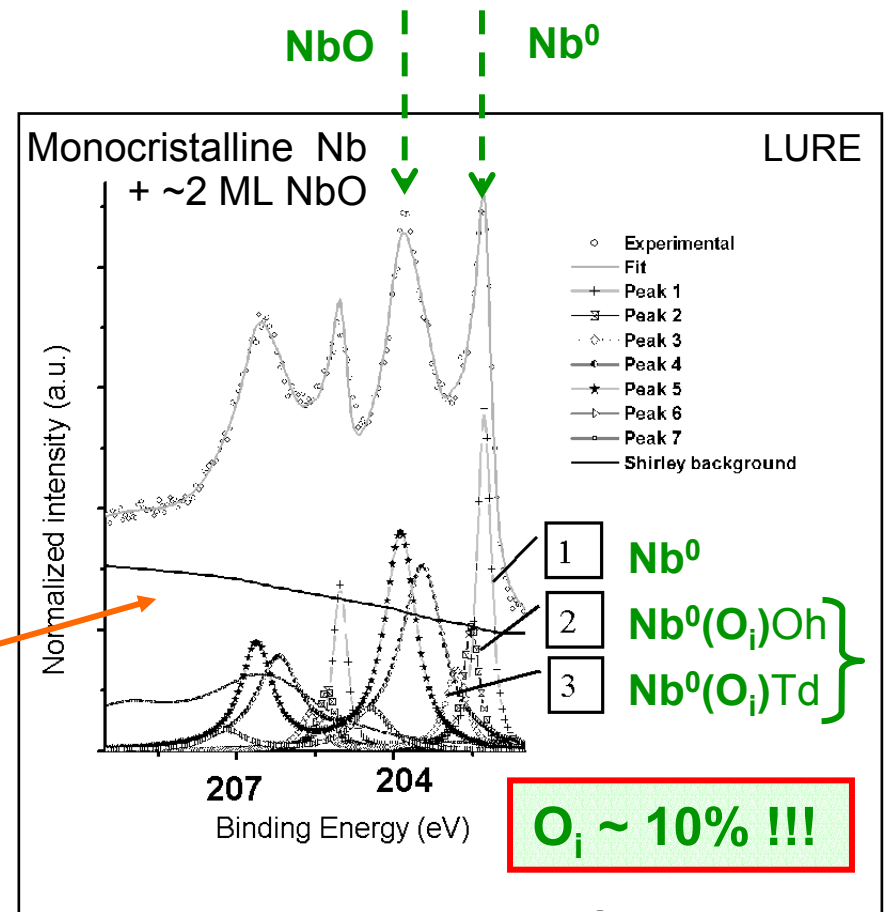
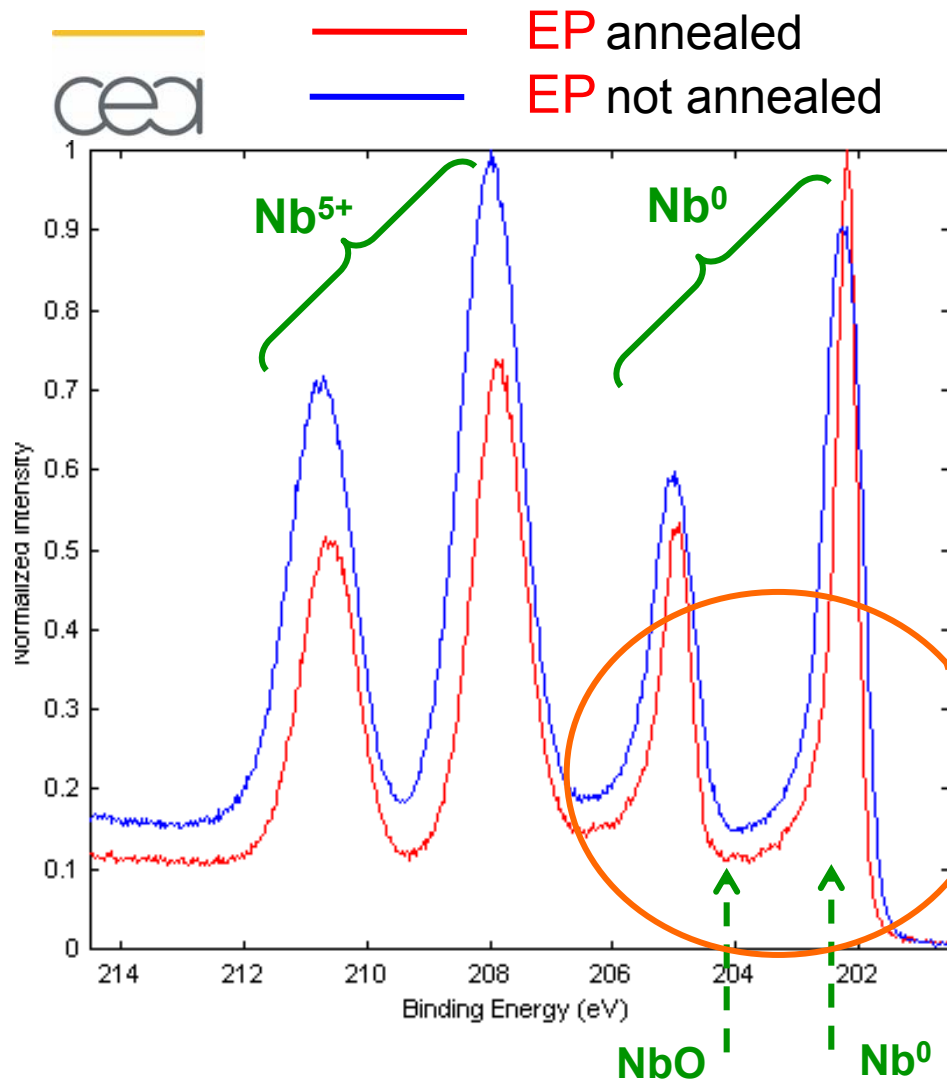


At least 6 statistically significant components...

# Photoemission : high resolution

Classical XPS: resoln~1eV

XPS with Synchrotron source

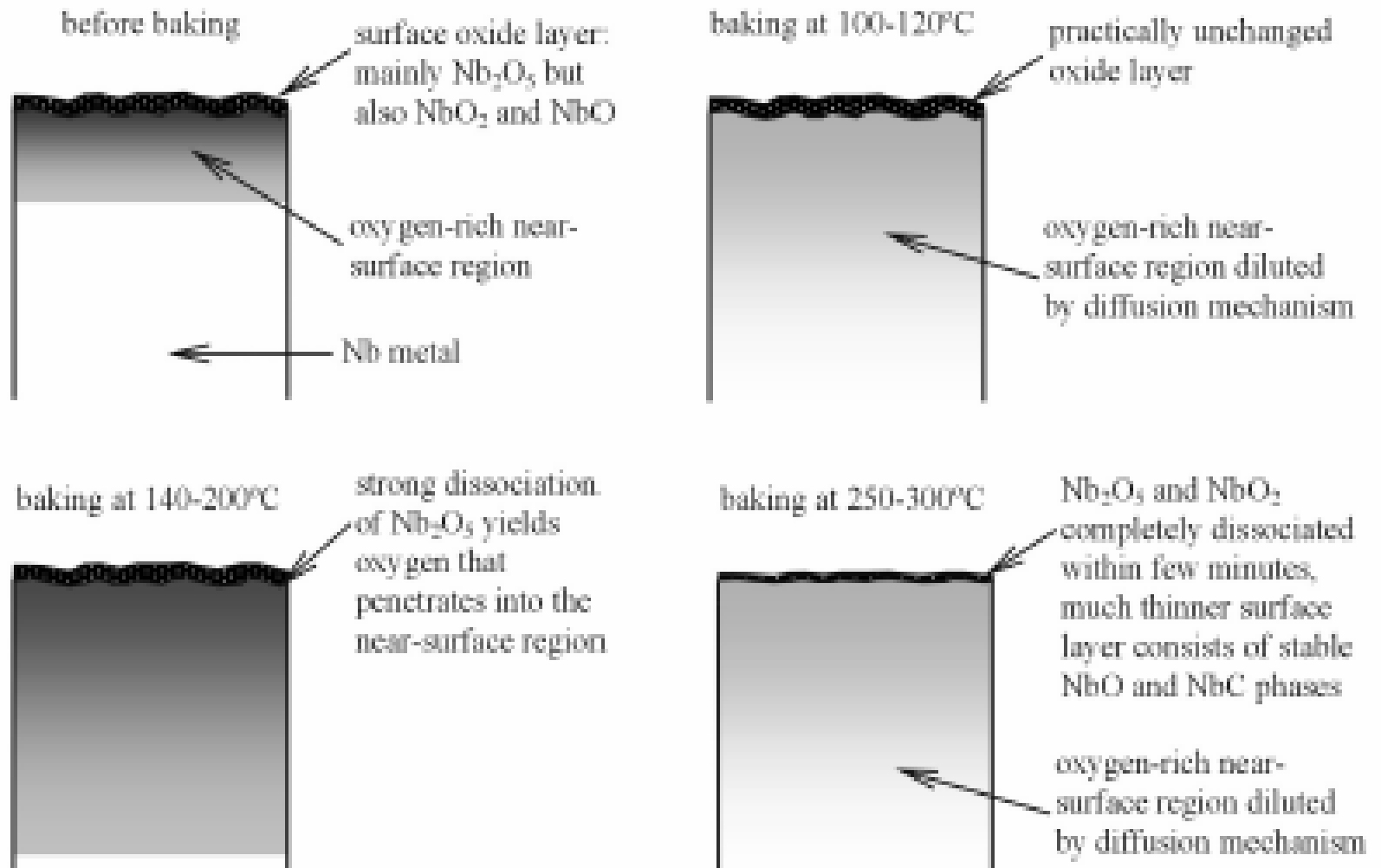


$[O_i]_{3nm} > \sim 200 \times [O_i]_{bulk} !!!$

# The “right” scenario: as inferred from XPS

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[Kowalski]  
[Antoine,  
Chincarini,  
Ma, ....]



# The O<sub>i</sub> (C<sub>i</sub>) scenario:

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■ Baking under vacuum : destruction of Nb<sub>2</sub>O<sub>5</sub> => defects, dangling bonds, O<sub>i</sub> => more localized states within the gap !!! [*Band theory !*]

■ Baking in air : oxide is reconstructed (increased).

**=> contradiction with the ITE model !?**

■ ∃ C<sub>i</sub> at metal-ox interface, poorly etched (neutral specie)

■ Nb carbide forms @ 180-200° C [*Kowalski, Ma, Antoine, Chincarini, ....*]

■ Observed appreciable degradation starting @ 180-200° C (T<sub>c</sub>, R<sub>S</sub> (10K), (depth ~1μm) [*Visentin*], but...

■ Degradation of R<sub>BCS</sub> [*Visentin, Kneisel*], & calculated T<sub>c</sub> & λ [*Giovati*], as soon as 90° C (but no observed slope modif<sup>n</sup> @ so low T<sub>p</sub><sup>o</sup>) (depth ~5 nm)

■ Some recovering starting @ ~ 250° C (Nb<sub>2</sub>O<sub>5</sub> = totally dissolved but carbides still there)

# Oxide thickness: EP vs BCP

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- After BCP : thickness ~ 5nm, serrated.
  - After EP : a lot of discrepancies in the literature !
- But
- Thickness of EP oxide: depends from time in the EP bath  
w/wt bias : 10 Volt => ~ 20 nm of oxide => dissolved / HF
  - There are some indications that EP contains more Oxygen /BCP (also Carbon)
    - By profiling SIMS, RBS, GDL [[Antoine](#)], XPS, AES [[Asano](#)] , but oxide or O<sub>i</sub>? hydrocarbide or C<sub>i</sub> ?
    - Indirect: magnetization experiments [[Casalbuoni](#), [Steffen](#)]

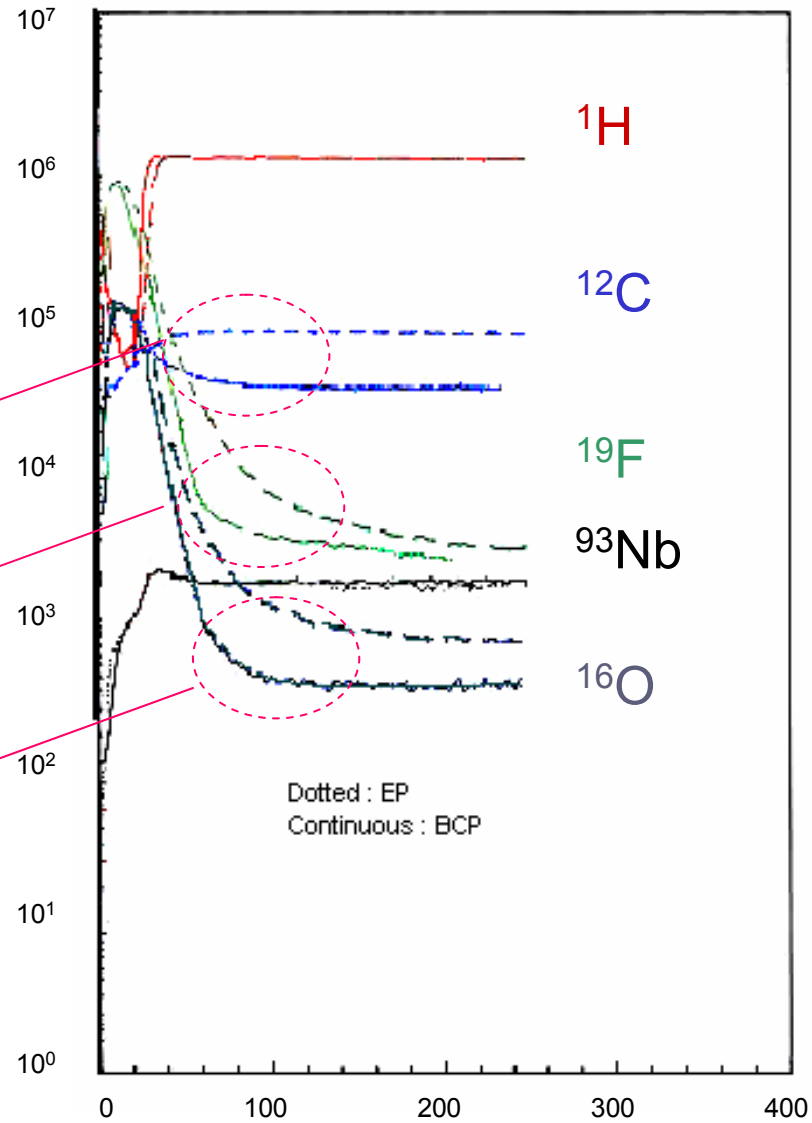
# Oxide thickness: EP vs BCP



SIMS

Secondary counts

EP more contaminated than BCP ?

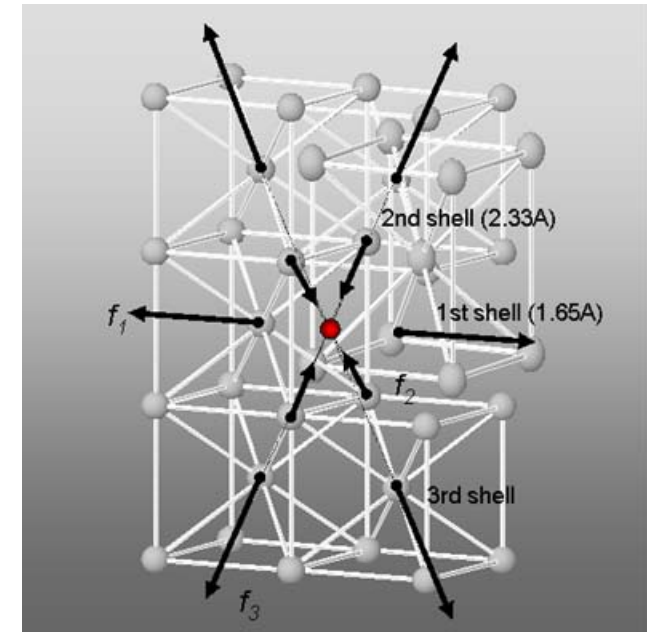
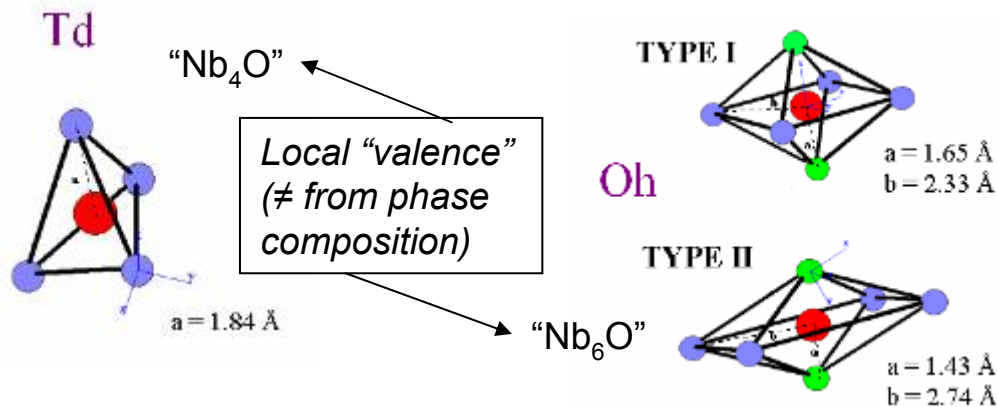


# Interstitial oxygens ( $O_i$ )

(sometimes referred as “suboxide” clusters)



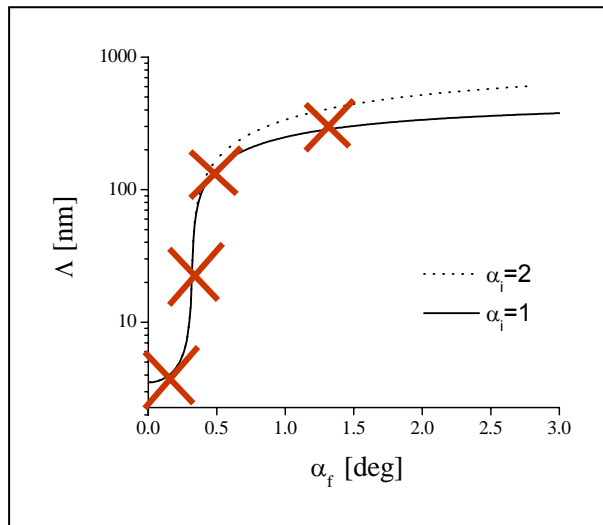
- Segregation near metal-oxyde interface
- $[O_i]$  ranging from ~10 At% [Arfaoui] to ~70 At% [Hellwig] ( $5/7=0.714\dots$ )
- Origin:
  - Upon oxydation :competition between oxidation/ $O_i$  injection [TB, Halbritter, Arfaoui, Hellwig...]
  - Thermal diffusion (upon cooling) [TB, ...]



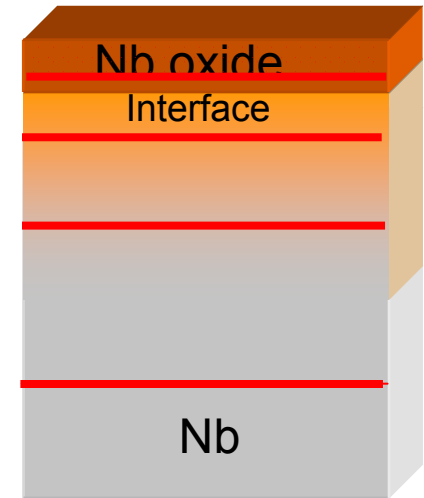
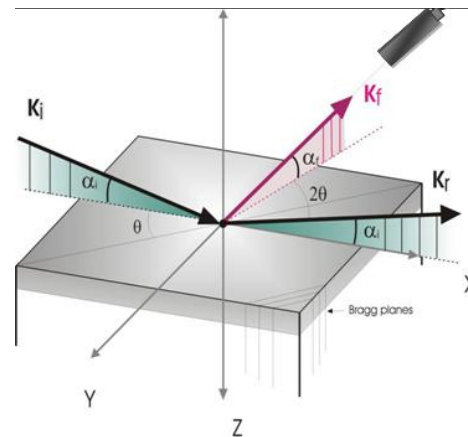
**“Local distortion” in the close neighborhood of randomly distributed defects (~1% O) : BCC → trigonal  $\omega$  phase, seen on Nb monocrystal by diffuse scattering [Dosch (bulk), Delheusy(surface, tbp)]**



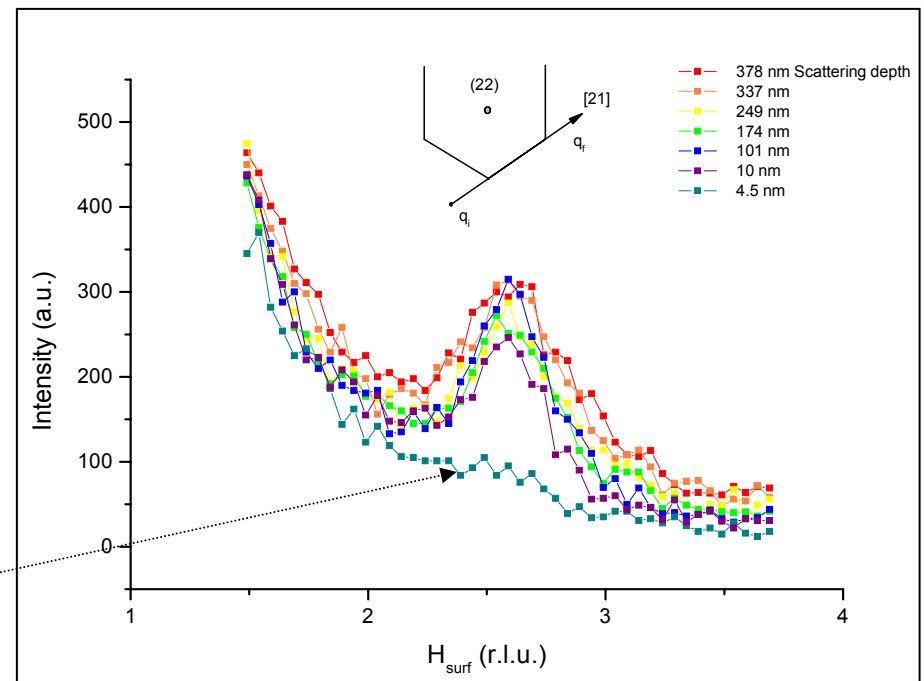
# Depth-sensitive diffuse scattering in the near surface region: first results



Scattering depth  $\Lambda = f(\alpha_f, \alpha_i)$



Diffuse scattering intensity evolution for different scattering depths.



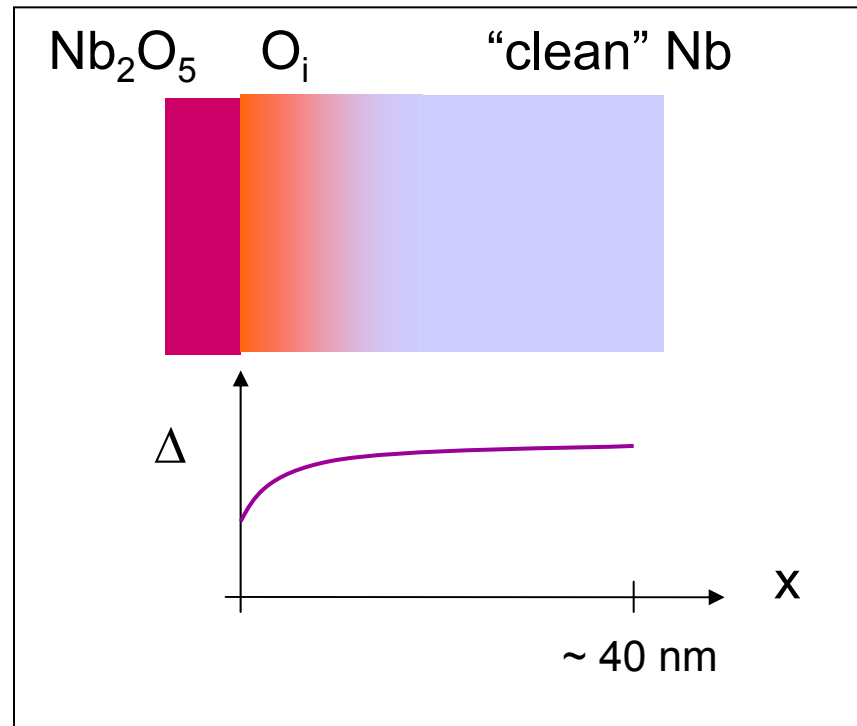
Inside the oxide : no signature of the distortion

# $O_i$ : So what !?

- How does  $O_i$  influence superconductivity ?
- $[O_i]$  might affect very locally the superconducting gap  $\Delta$  ( $d_{\text{char}} \sim 1\text{nm}$ )  
[Gurevich]



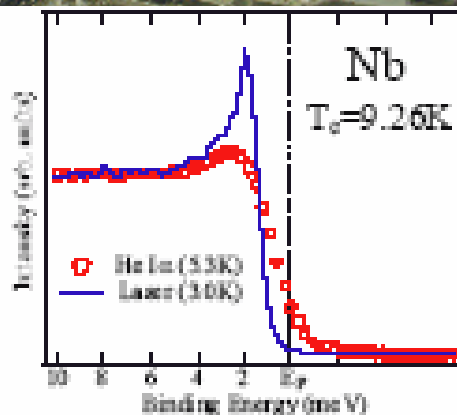
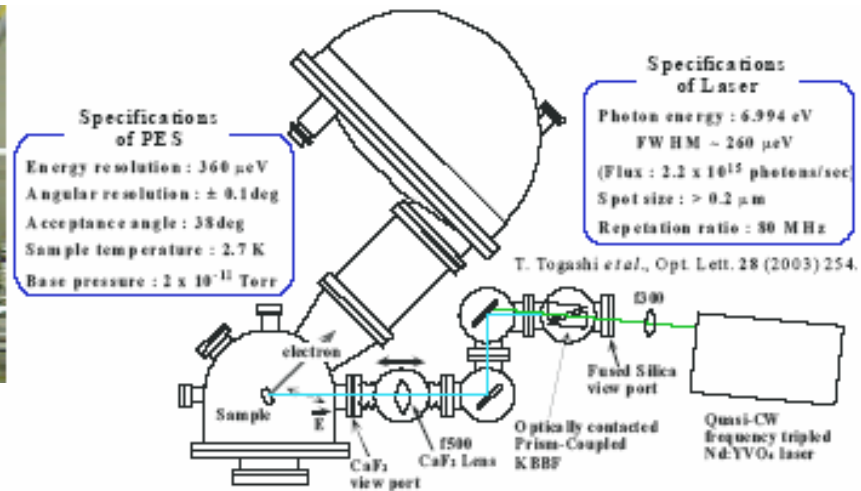
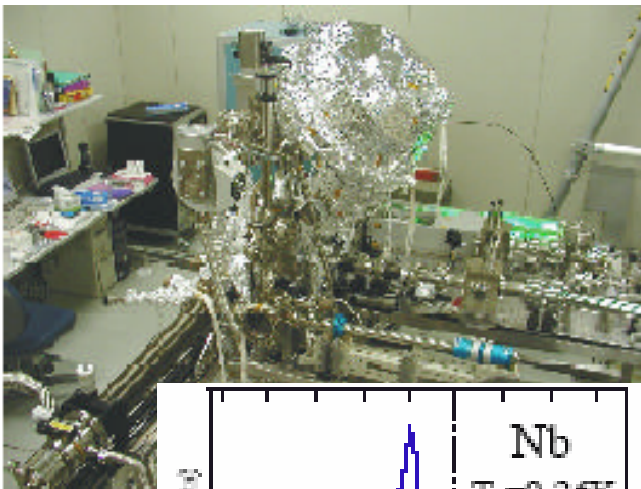
$$R_s \sim e^{-\Delta/T}$$



# $O_i$ : So what !?

- How does  $O_i$  influence superconductivity ?
- $[O_i]$  might affect very locally the superconducting gap  $\Delta$  ( $d_{\text{char}} \sim 1\text{nm}$ ) [Gurevich]
- Need for a nm sensitive probe !

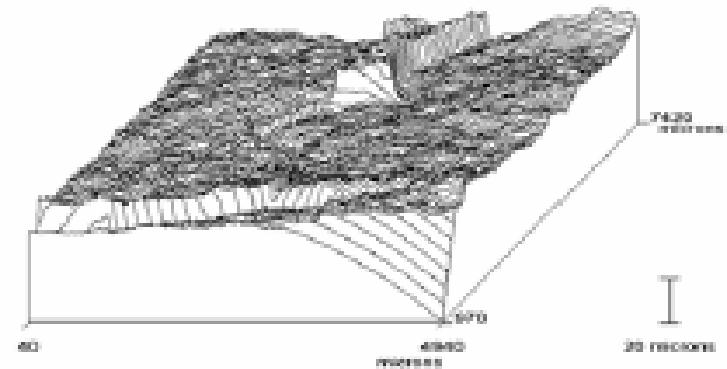
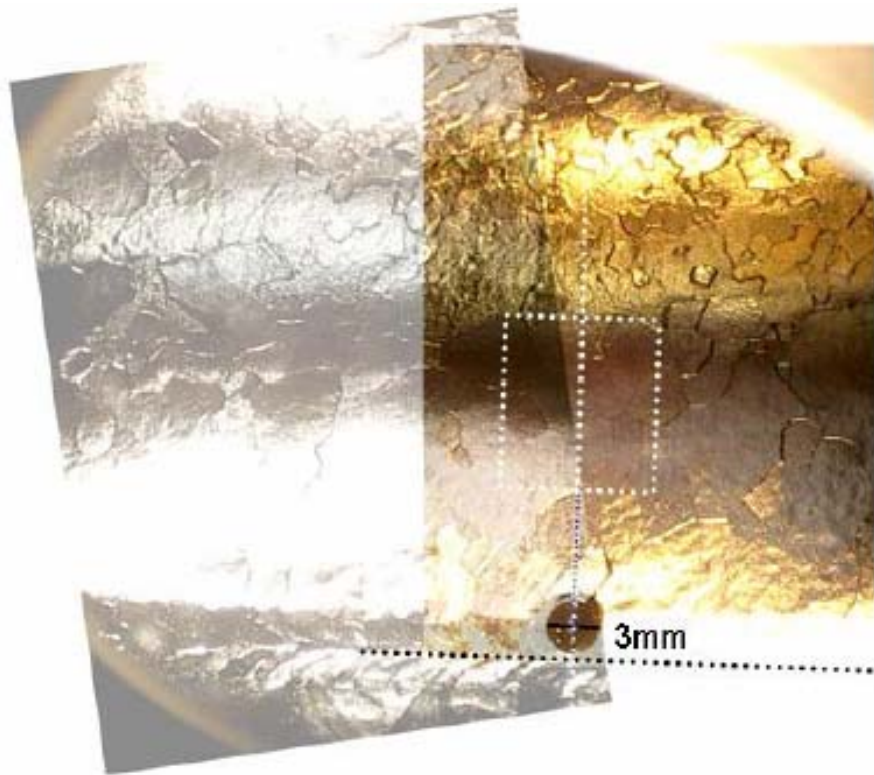
=> **Ultrahigh resolution laser photoemission spectrometer**



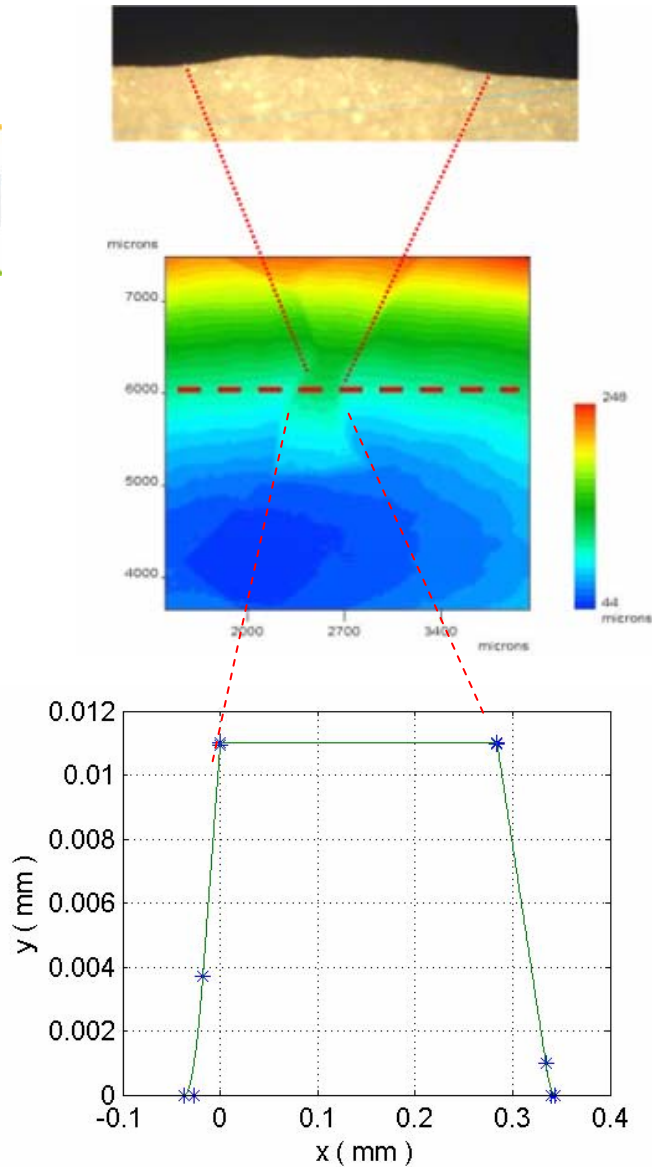
Comparison of the spectra of superconducting state of niobium between Laser PES and He discharge lamp PES

**Angle resolved method + in situ baking => profiling is possible with nm resolution !** [Kiss]

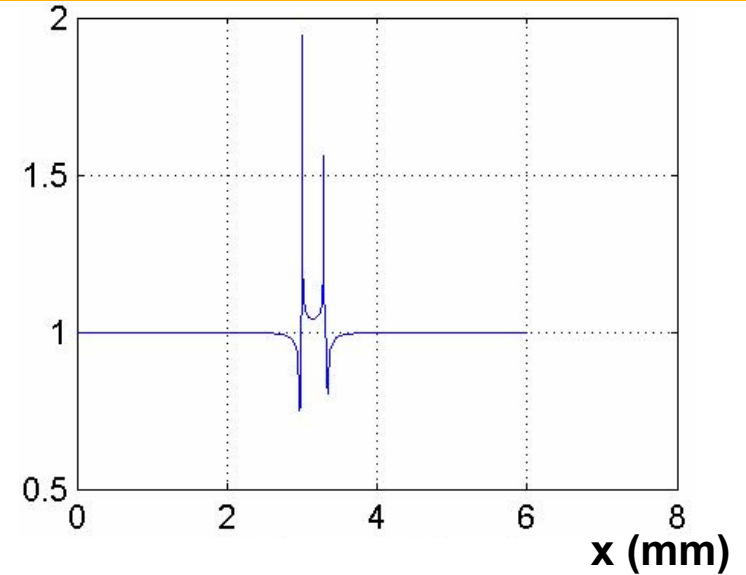
# Morphology @ grain edges



# Replica @ the quench site...

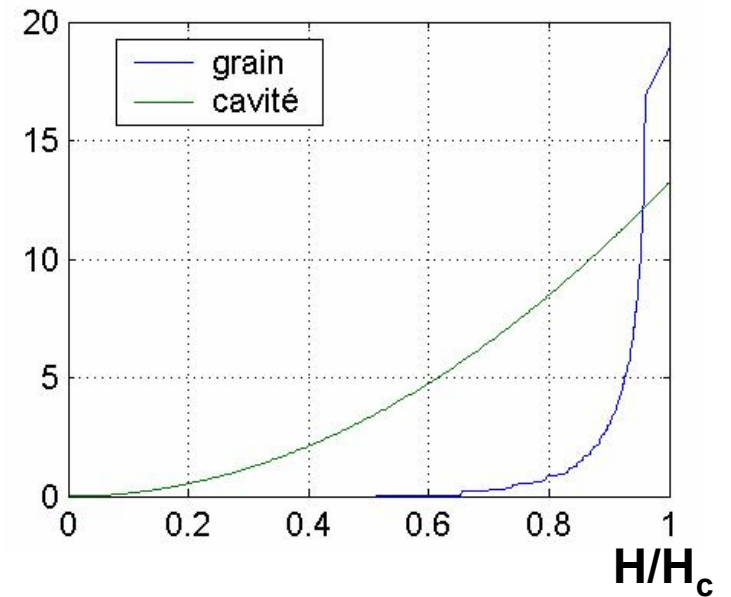


$H/\langle H \rangle$



P (W)

Dissipated power  
( $R_s \sim 2m\Omega$ )



# Replica @ the quench site...

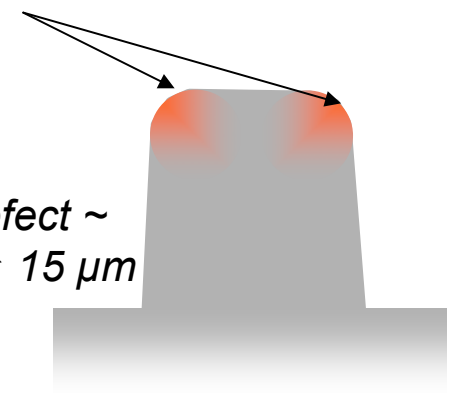


## Thermal behavior :

- Edges thermally stabilized until  $T \sim 5.35$  K and  $W \sim 142$  mW
- $T < 9.2$  K but  $H > H_c$
- When  $W \sim 143$  mW  $\Rightarrow$  **Quench !**

Normal cond. zone

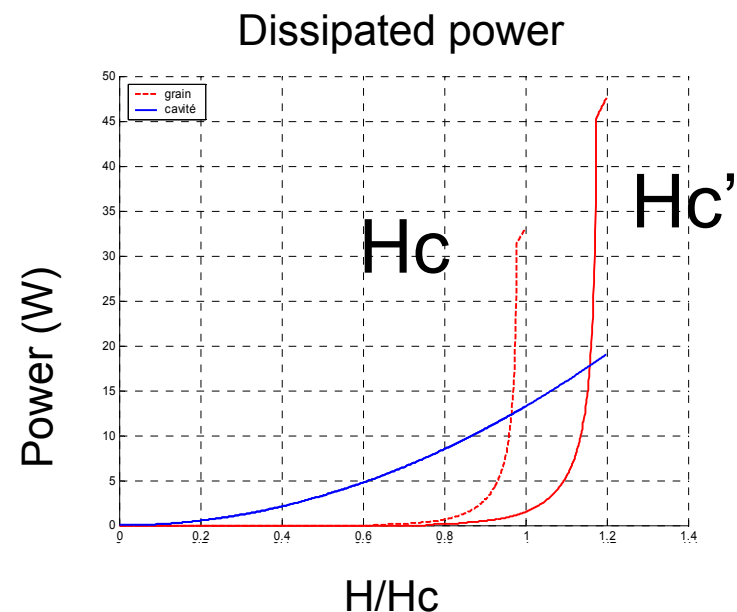
Size of the defect  $\sim$   
 $\rightarrow 550 \mu\text{m} \times \uparrow 15 \mu\text{m}$



**morphology = trigger / thermal behavior = quench.**

## Baking : $\uparrow H_c$

- Modelling of the **defect contribution** compared to the **contribution of the whole cavity** for  $H_c$ .
- and  $H_c' > H_c$ .



**Local morphology: rather quench than Q-slope ?!**

# Replica @ the quench site

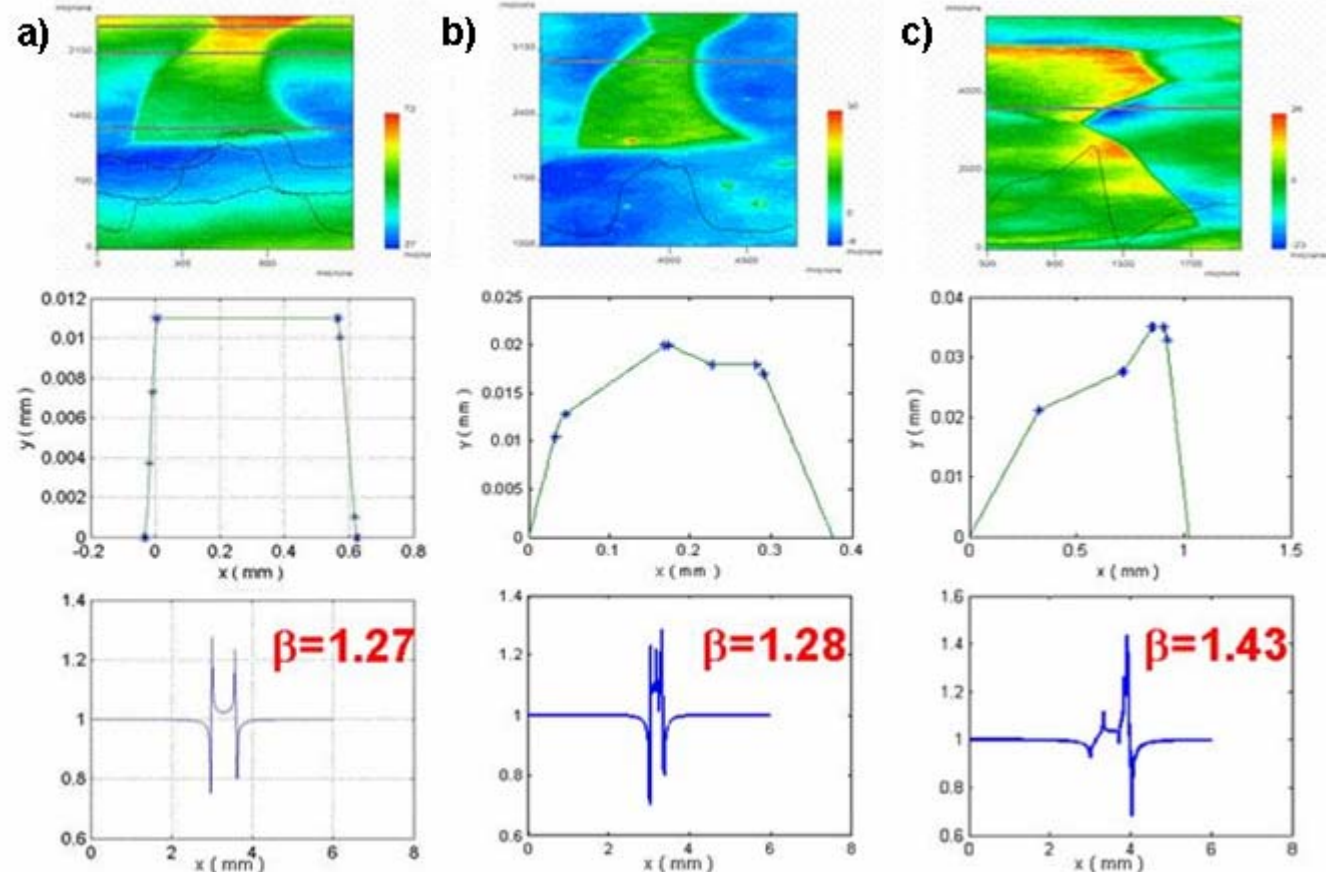
- a) first quench site,
- b) same area after 20  $\mu\text{m}$  (quench site @ a new location)
- c) new quench location.



Contour line of replicas

Modeling of the edge profile

$\beta$  (field enhancement factor)



**Local morphology is consistent for explaining the quench**



# Conclusions about the Q-slope

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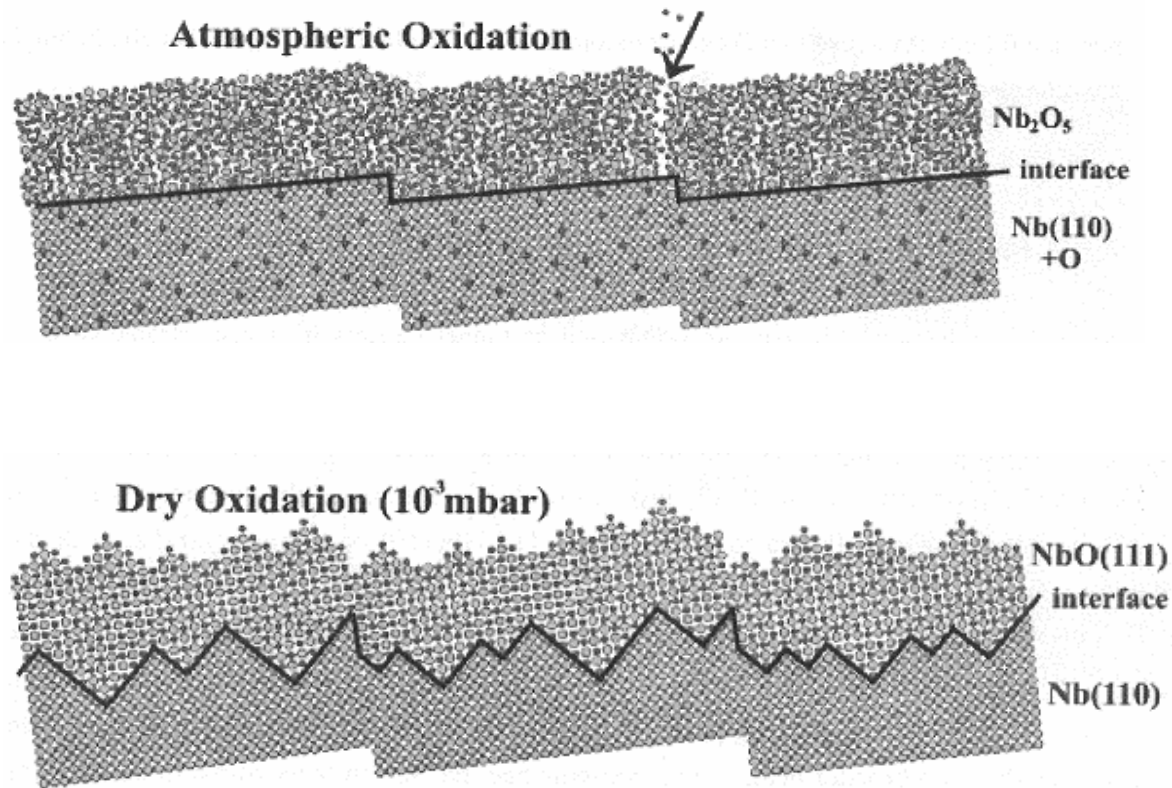
- Surface studies allow to rule out several hypothesis : adsorbed layer, modification of the oxide layer, hydrogen...and possibly ITE, morphology.
- Interstitial oxygen is the best suspect.
- Possible influence of Carbon (source = interstitial rather than hydrocarbon).
- There are (difficult) ways to check the variation of the oxygen distribution and/or to measure locally the superconducting gap.
- Morphology seems to better explain quench than slope

**Further theoretical developments are needed**



# Oxygen ....

Clean interface ?



from [ Hellwig, 2000]

# Segregation : mecanism

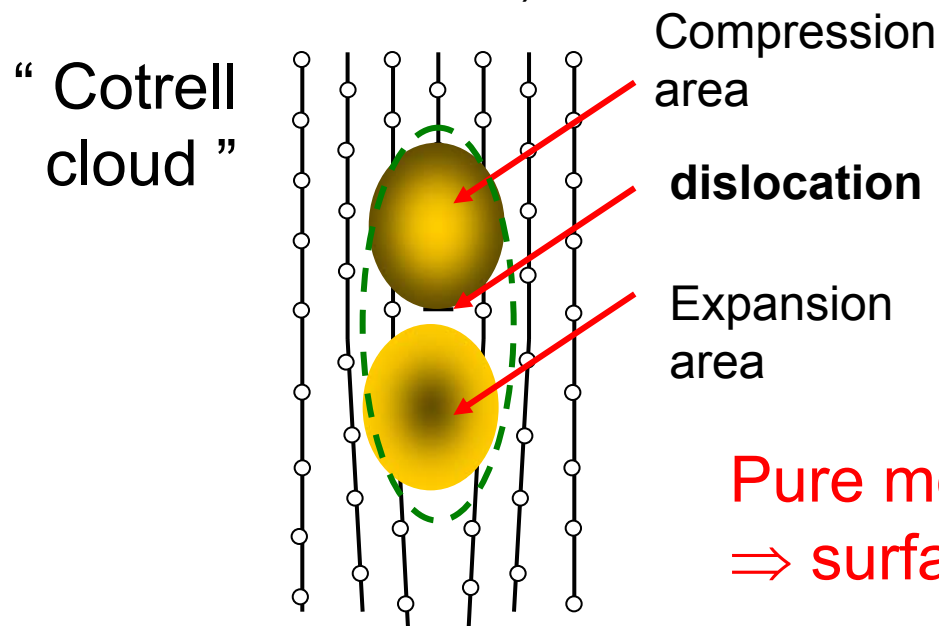
■ defect in lattice  $\Rightarrow$  lattice distorsion (elastic strain)



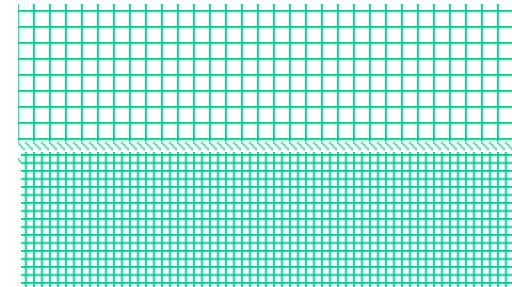
■ light impurities interact with defect (interaction energy  $\Delta W$ )

$$\Delta W_{\text{interface}} > \Delta W_{\text{dislocation}} > \Delta W_{\text{isolated atoms/vacancies}}$$

■ + preferential diffusion in “disordered” regions (interaction with vacancies)



**Interface : ~ an array of dislocation**

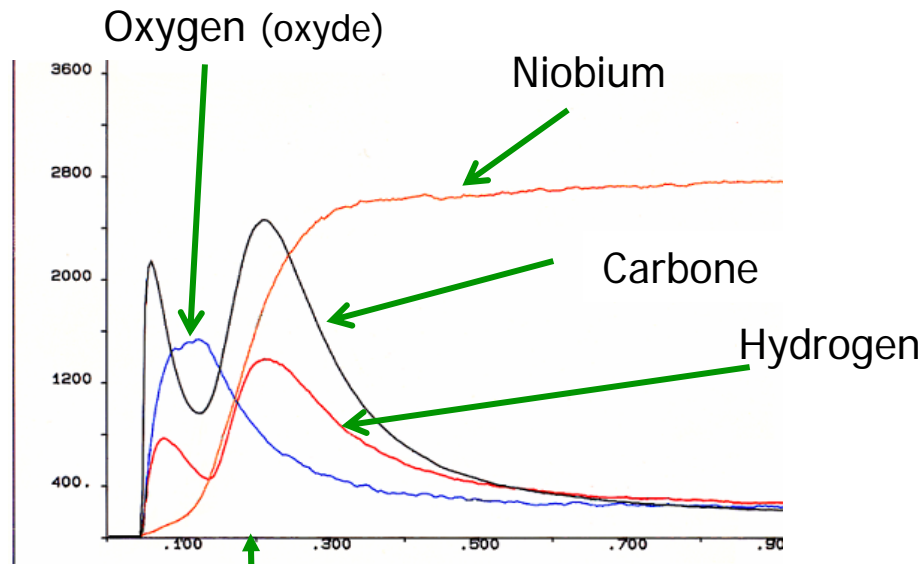


Pure metals : not many “defects” in bulk  
 $\Rightarrow$  surface, interface segregation

# Surface segregation : experimental evidences

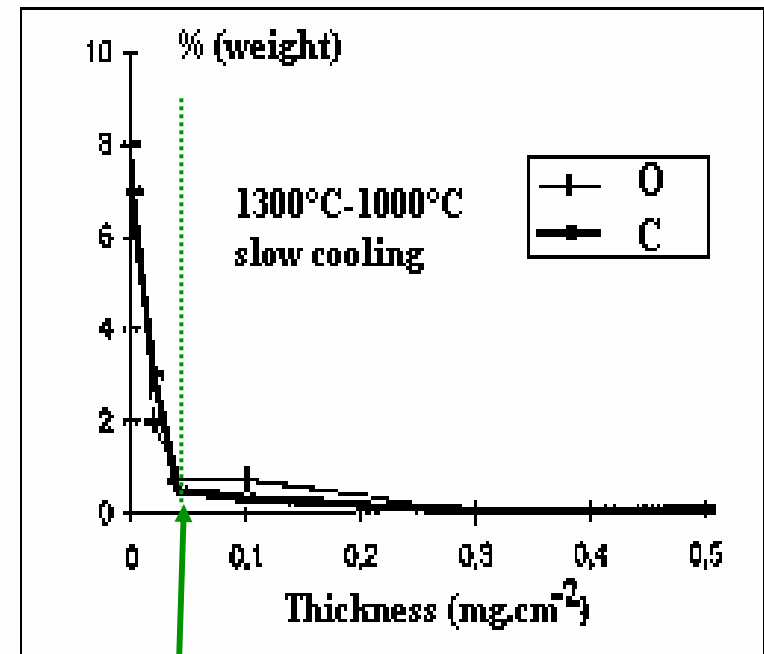


■ Glow Discharge Luminescence (GDL)



~ oxide-metal interface

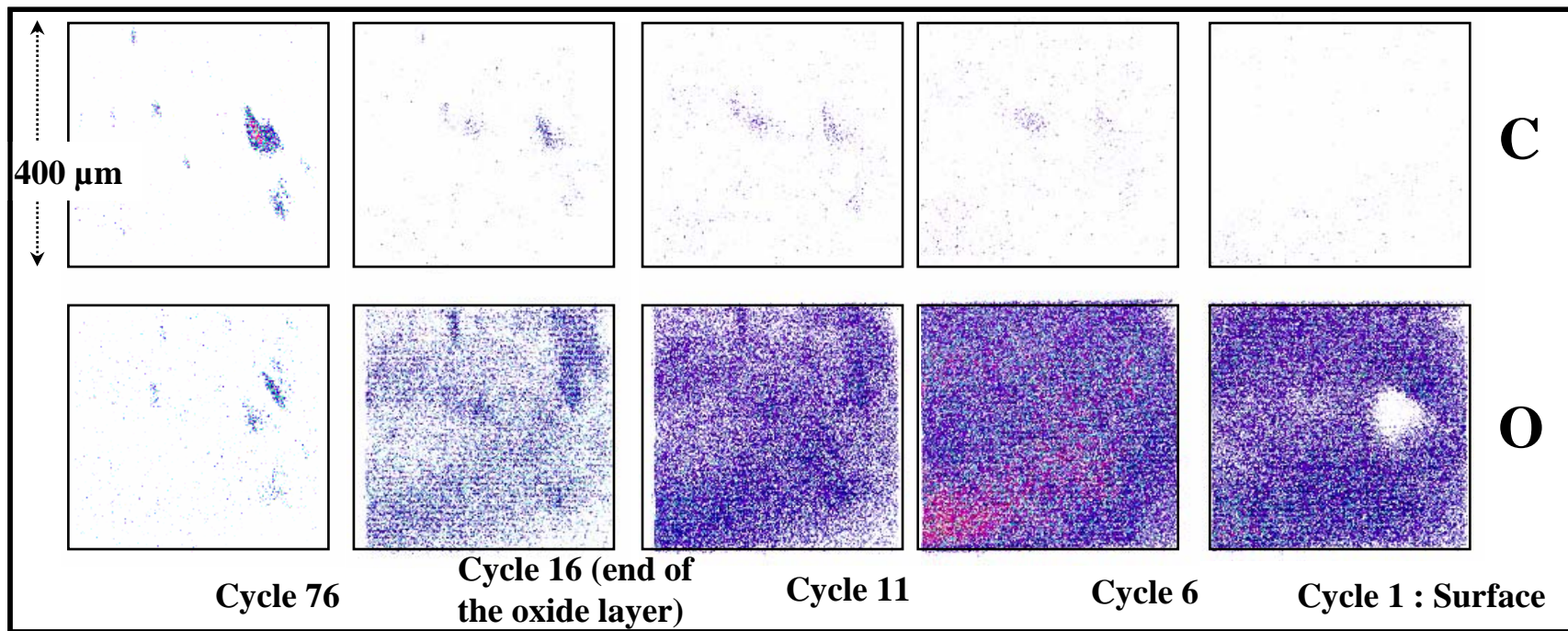
■ Nuclear resonant reactions



~ oxide(Ti)-metal interface

# Local segregation : experimental evidences

■ SIMS(TOF-SIMS), UHV



# Niobium surface studies...



## Effect of HPR

■ ESCA

■ TOF-SIMS

